

/ Descriptions

WR06S ММ Ё SQS æ М ы s ll 1 Silicon PNP transistor in a TO-3P Plastic Package.

/ Features

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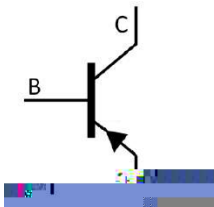
Low leakage current, high current gain bandwidth product, Complementary to TIP35C.

/ Applications

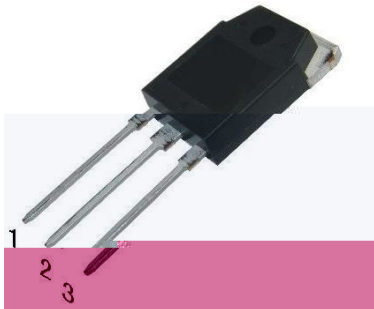
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Amplifier and switching applications.

/ Equivalent Circuit



/ Pinning



PIN1 χ Base PIN 2 χ Collector PIN 3 χ Emitter

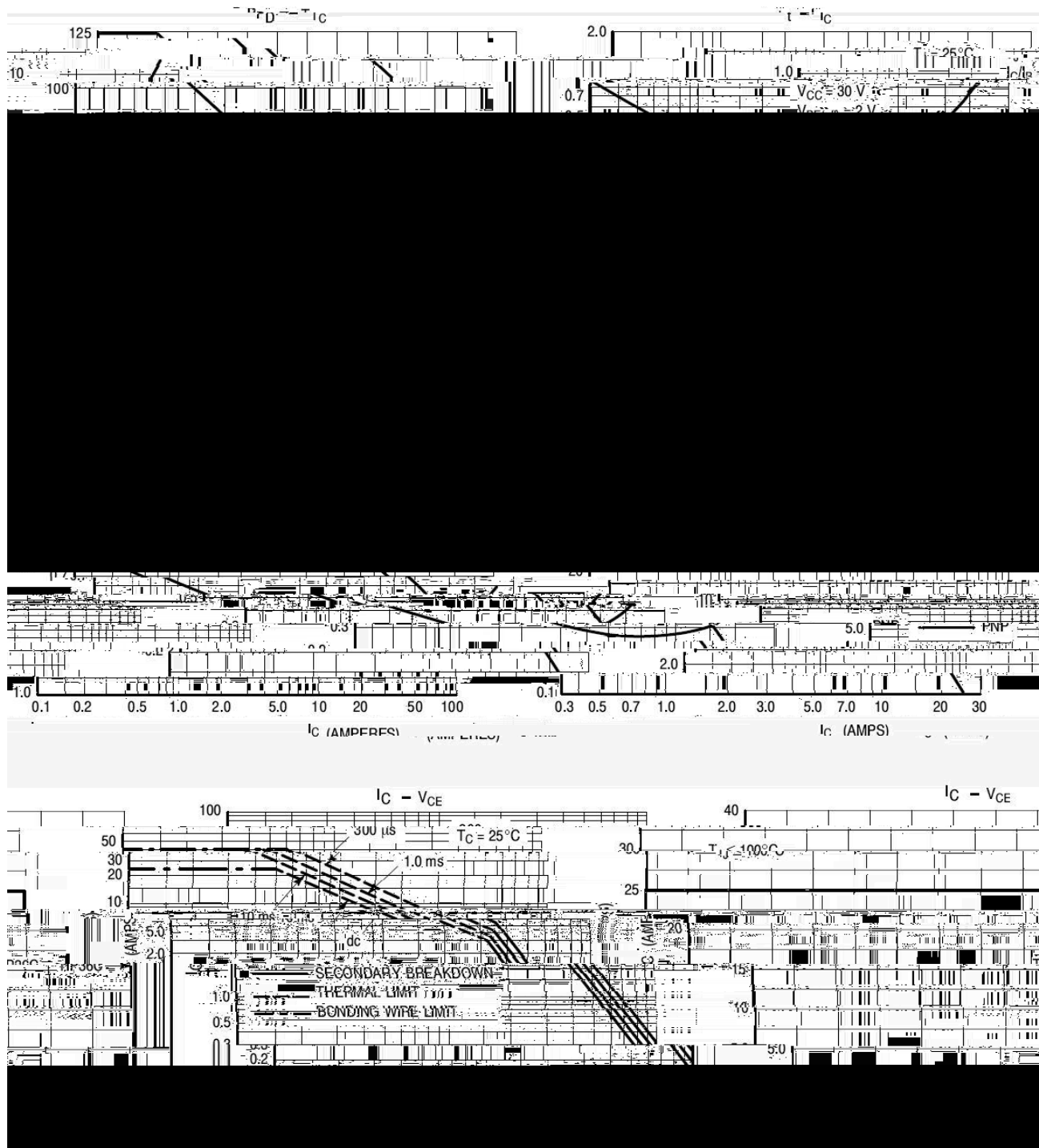
/ h_{FE} Classifications & Marking

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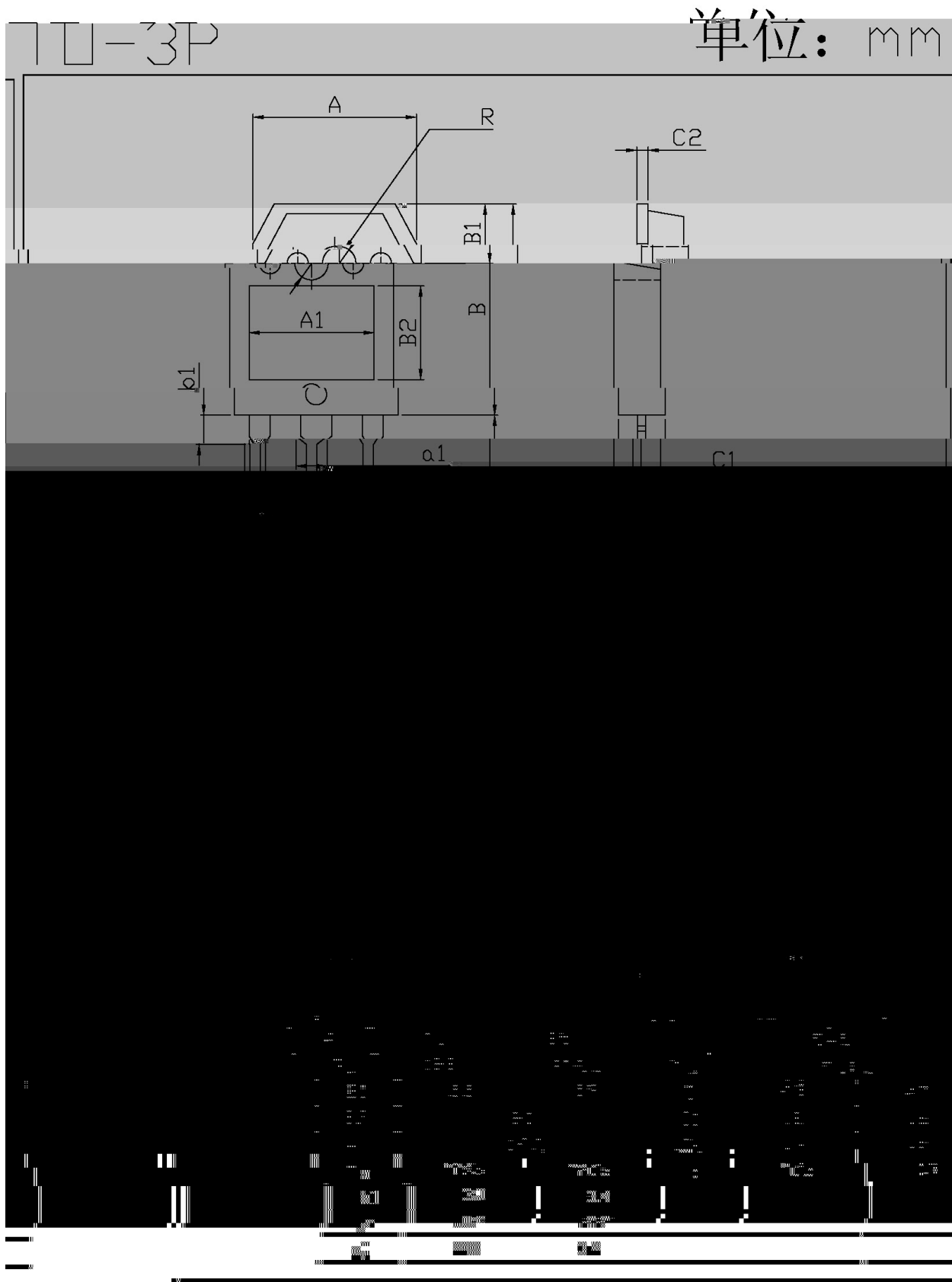
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-100	V
Collector to Emitter Voltage	V_{CEO}	-100	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collector Current - Continuous	I_C	-25	A
Peak Collector Current	I_{CM}	-50	A
Base Current	I_B	-5	A
Total Power Dissipation	P_{tot}	125	W
Junction Temperature	T_J	175	°C
Storage Temperature Range	T_{stg}	-65 ~ 150	°C
Thermal Resistance Junction	R_{thj}	1	/W

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CEO}	$V_{CE}=-60V$ $I_B=0$			-1	mA
Collector Cut-Off Current	I_{CES}	$V_{CE}=-60V$ $V_{BE}=0$			23a	

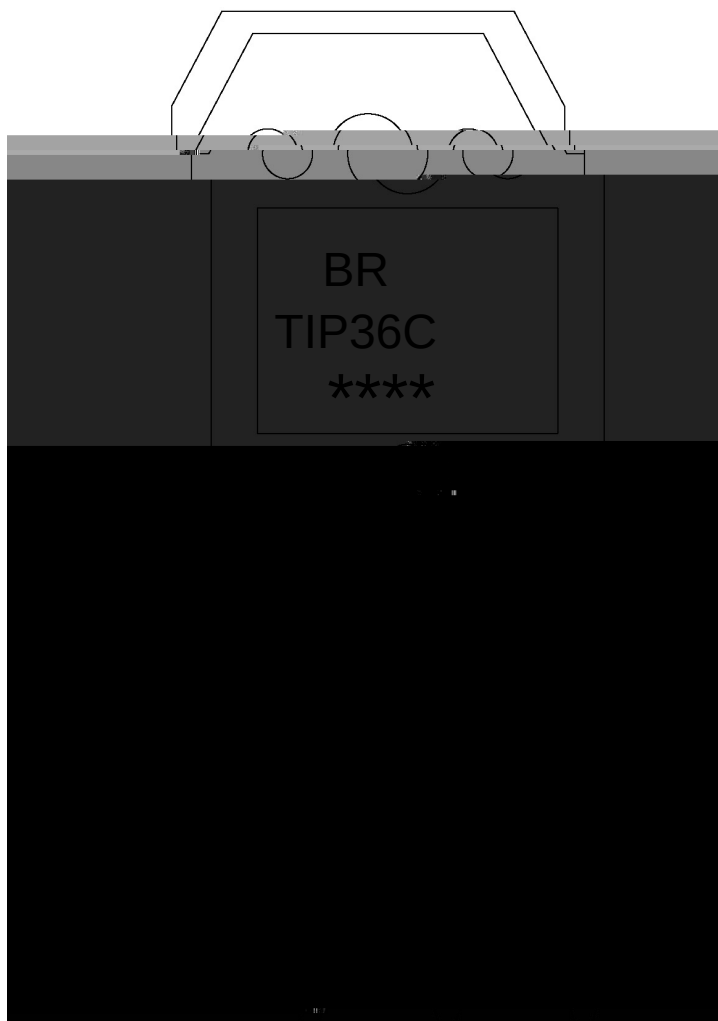
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



公司代码

EU:

WLS69F

Note:

BR:

TIP36C:

****:

公司代码

WLS69F

Company Code.

Product Type.

Lot No. Code, code change with Lot No.

TIP36C
Rev.E Mar.-2016